

GSDBAV70

Monolithic Dual Switching Diode Common Anode

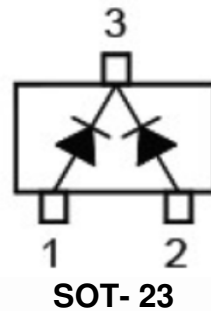
Product Description

Switching Diode 200mA / 75V

Features

- Low forward voltage
- For high-speed switching applications
- Halogen-free parts

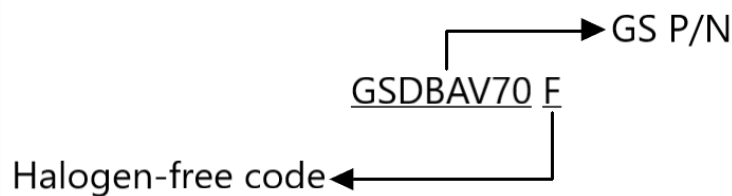
Packages



Marking Information

Part Number	Package	Part Marking
GSDBAV70F	SOT-23	A4

Ordering Information



Part Number	Package	Quantity
GSDBAV70F	SOT-23	3000 PCS

Maximum Ratings

(T_A=25°C Unless otherwise noted)

Symbol	Conditions	Value	Unit
V _{RRM}	Repetitive Peak Reverse Voltage	100	V
V _R	Reverse Voltage	75	V
I _F	Forward Current	200	mA
I _{FSM}	Peak Forward Surge Current, t = 1s t = 1μs	1 2	A
P _D	Total Power Dissipation(Note1)	350	mW
T _J	Junction Temperature	150	°C
T _{STG}	Storage Temperature Range	-55 to +150	°C

Electrical Characteristics

(T_A=25°C Unless otherwise noted)

Symbol	Conditions	Max	Unit
V _F	Forward Voltage (I _F =1.0mA)	715	mV
	(I _F =10mA)	855	
	(I _F =50mA)	1000	
	(I _F =150mA)	1250	
I _R	Reverse Current , V _R =25V	30	nA
	Reverse Current , V _R =75V	2.5	
	Reverse Current , (V _R =25V, T _J =150°C)	60	μA
	Reverse Current , (V _R =75V, T _J =150°C)	100	
C _d	Diode Capacitance (V _R =0V, f=1.0MHz),	2	pF
T _{rr}	Reverse Recovery Time I _F =10mA, V _R =6V , I _{rr} =1mA, R _L =100Ω	4	ns

Typical Characteristics

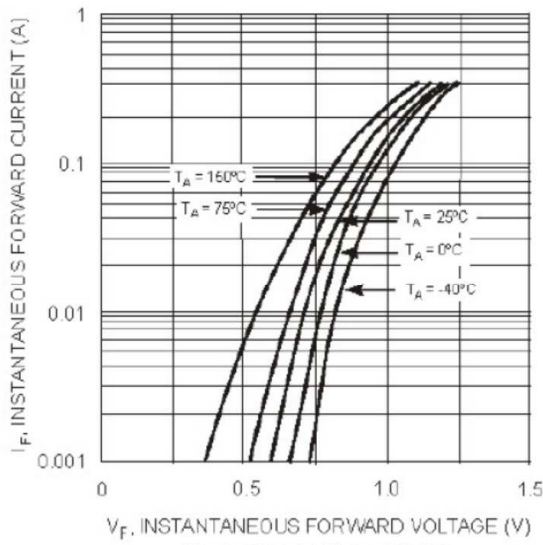


Fig. 1 Forward Characteristics

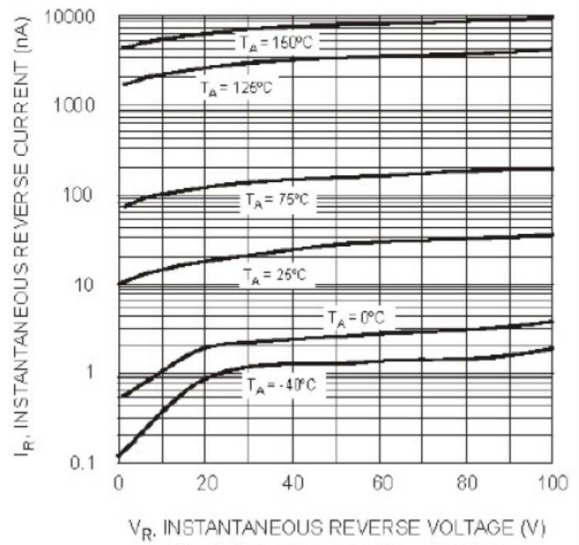


Fig. 2 Typical Reverse Characteristics

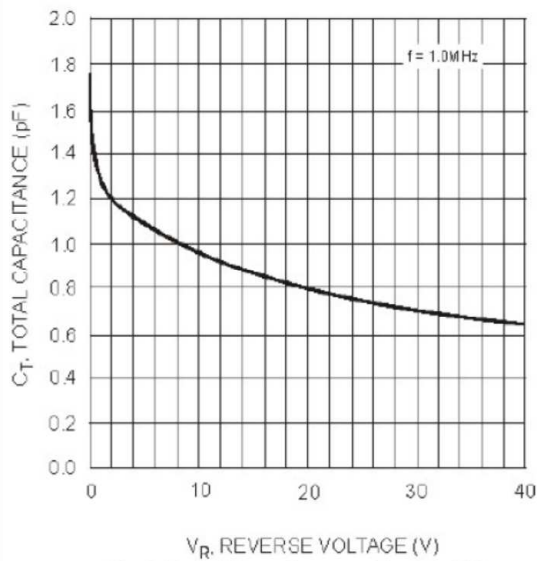


Fig. 3 Typical Capacitance vs. Reverse Voltage

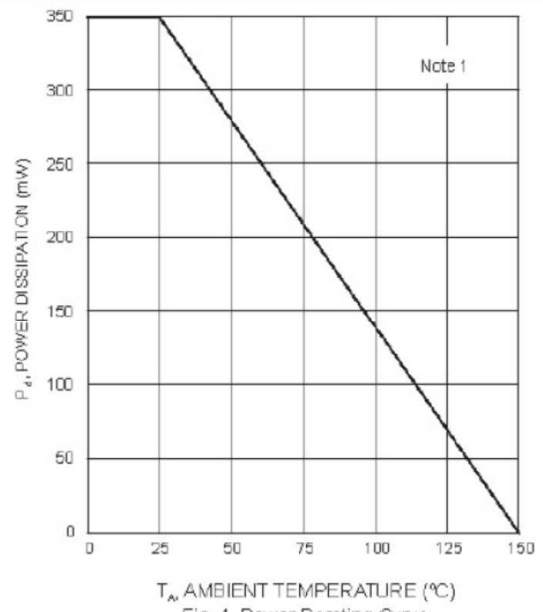
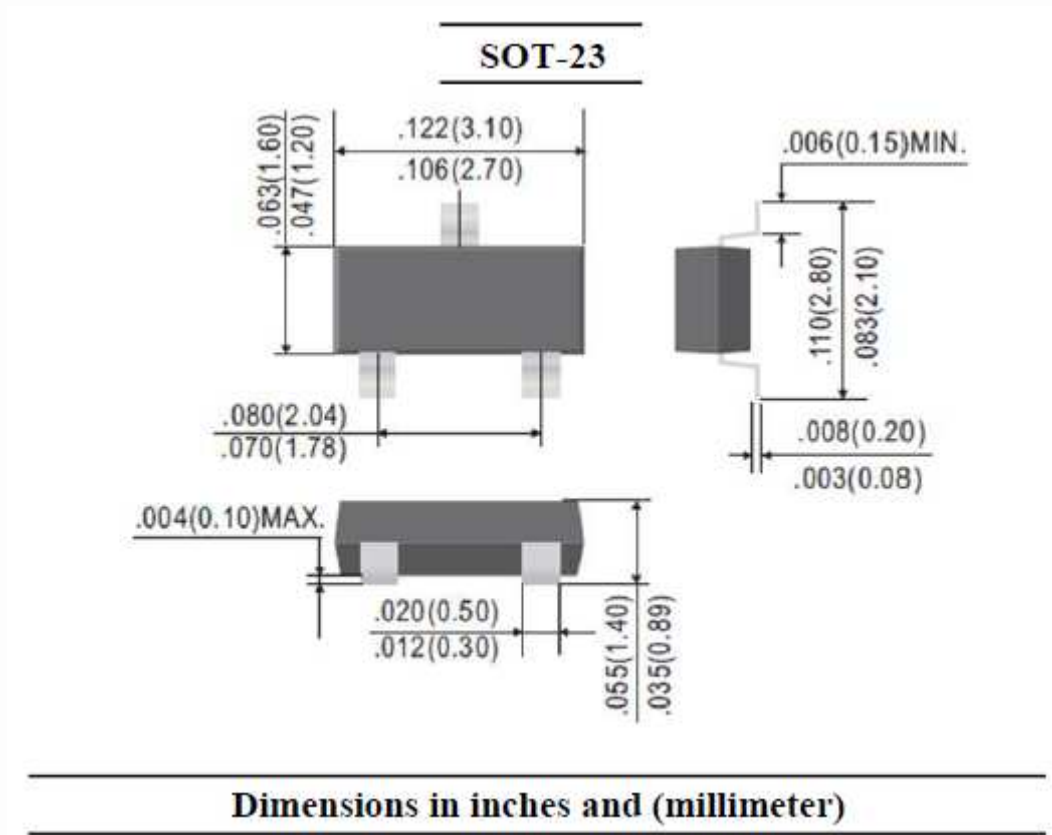


Fig. 4 Power Derating Curve





Package Dimension





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